

# ZXTD4591AM832

## MPPS™ Miniature Package Power Solutions COMPLEMENTARY DUAL 40V HIGH PERFORMANCE TRANSISTOR

### SUMMARY

**NPN Transistor** —  $V_{CE0} = 40V$ ;  $R_{SAT} = 195m\Omega$ ;  $I_C = 2.5A$

**PNP Transistor** —  $V_{CE0} = -40V$ ;  $R_{SAT} = 350m\Omega$ ;  $I_C = -2A$

### DESCRIPTION

Packaged in the new innovative 3mm x 2mm MLP (Micro Leaded Package), these high performance NPN/PNP combination dual transistors offer lower on state losses making them ideal for use in DC-DC circuits and various driving and power-management functions.

Users will also gain several other **key benefits**:

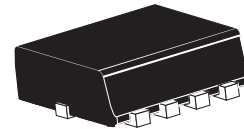
**Performance capability equivalent to much larger packages**

**Improved circuit efficiency & power levels**

**PCB area and device placement savings**

**Lower package height (0.9mm nom)**

**Reduced component count**



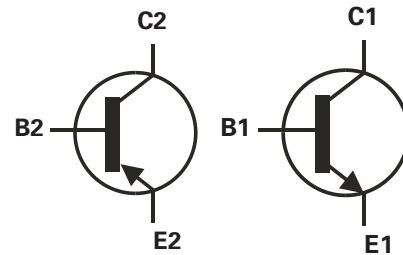
3mm x 2mm Dual Die MLP

### FEATURES

- Low Saturation Voltage (500mV max @1A)
- $H_{FE}$  specified up to 2A
- $I_C = 2.5A$  Continuous Collector Current
- 3mm x 2mm MLP

### APPLICATIONS

- DC - DC Converters
- Power switches
- Motor control
- LED Backlighting circuits



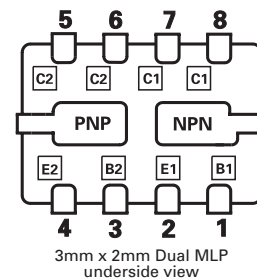
### ORDERING INFORMATION

DEVICE	REEL L	TAPE WIDTH	QUANTITY PER REEL
ZXTD4591AM832TA	7''	8mm	3000
ZXTD4591AM832TC	13''	8mm	10000

### DEVICE MARKING

91A

### PINOUT



3mm x 2mm Dual MLP  
underside view

# ZXTD4591AM832

## ABSOLUTE MAXIMUM RATINGS.

PARAMETER	SYMBOL	NPN	PNP	UNIT
Collector-Base Voltage	$V_{CBO}$	40	-40	V
Collector-Emitter Voltage	$V_{CEO}$	40	-40	V
Emitter-Base Voltage	$V_{EBO}$	5	-5	V
Peak Pulse Current	$I_{CM}$	3	-3	A
Continuous Collector Current (a)(f)	$I_C$	2	-1.5	A
Continuous Collector Current (b)(f)	$I_C$	2.5	-2.0	A
Base Current	$I_B$	300		mA
Power Dissipation at TA=25°C (a)(f) Linear Derating Factor	$P_D$	1.5 12		W mW/°C
Power Dissipation at TA=25°C (b)(f) Linear Derating Factor	$P_D$	2.45 19.6		W mW/°C
Power Dissipation at TA=25°C (c)(f) Linear Derating Factor	$P_D$	1 8		W mW/°C
Power Dissipation at TA=25°C (d)(f) Linear Derating Factor	$P_D$	1.13 9		W mW/°C
Power Dissipation at TA=25°C (d)(g) Linear Derating Factor	$P_D$	1.7 13.6		W mW/°C
Power Dissipation at TA=25°C (e)(g) Linear Derating Factor	$P_D$	3 24		W mW/°C
Storage Temperature Range	$T_{stg}$	-55 to +150		°C
Junction Temperature	$T_j$	150		°C

## THERMAL RESISTANCE

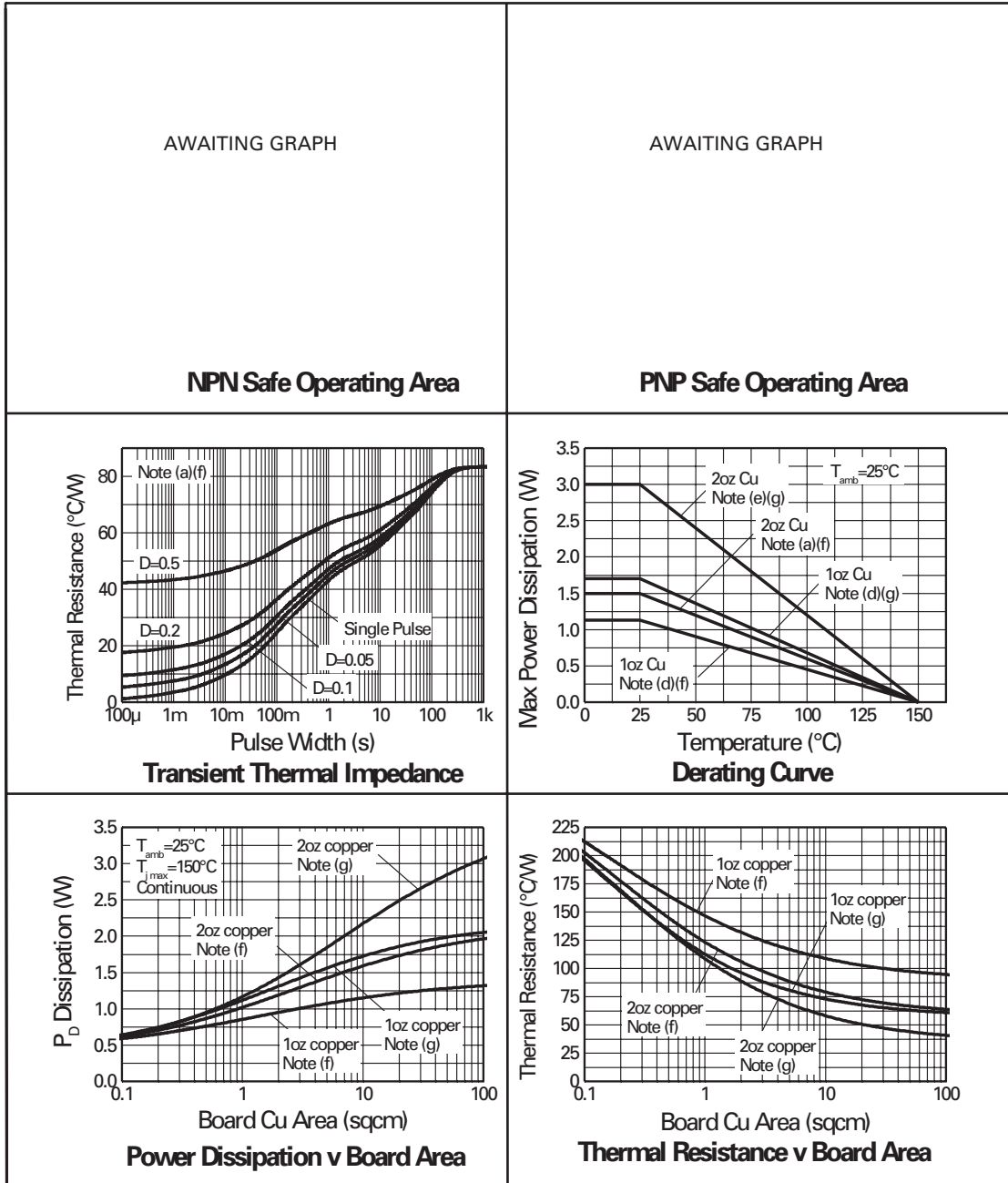
PARAMETER	SYMBOL	VALUE	UNIT
Junction to Ambient (a)(f)	$R_{\theta JA}$	83.3	°C/W
Junction to Ambient (b)(f)	$R_{\theta JA}$	51	°C/W
Junction to Ambient (c)(f)	$R_{\theta JA}$	125	°C/W
Junction to Ambient (d)(f)	$R_{\theta JA}$	111	°C/W
Junction to Ambient (d)(g)	$R_{\theta JA}$	73.5	°C/W
Junction to Ambient (e)(g)	$R_{\theta JA}$	41.7	°C/W

### Notes

- (a) For a dual device surface mounted on 8 sq cm single sided 2oz copper on FR4 PCB, in still air conditions **with all exposed pads attached**. The copper area is split down the centre line into two separate areas with one half connected to each half of the dual device.
- (b) Measured at  $t < 5$  secs for a dual device surface mounted on 8 sq cm single sided 2oz copper on FR4 PCB, in still air conditions **with all exposed pads attached**. The copper area is split down the centre line into two separate areas with one half connected to each half of the dual device.
- (c) For a dual device surface mounted on 8 sq cm single sided 2oz copper on FR4 PCB, in still air conditions **with minimal lead connections only**.
- (d) For a dual device surface mounted on 10 sq cm single sided 1oz copper on FR4 PCB, in still air conditions **with all exposed pads attached attached**. The copper area is split down the centre line into two separate areas with one half connected to each half of the dual device.
- (e) For a dual device surface mounted on 85 sq cm single sided 2oz copper on FR4 PCB, in still air conditions **with all exposed pads attached attached**. The copper area is split down the centre line into two separate areas with one half connected to each half of the dual device.
- (f) For a dual device with one active die.
- (g) For dual device with 2 active die running at equal power.
- (h) Repetitive rating - pulse width limited by max junction temperature. Refer to Transient Thermal Impedance graph.
- (i) The minimum copper dimensions required for mounting are no smaller than the exposed metal pads on the base of the device as shown in the package dimensions data. The thermal resistance for a dual device mounted on 1.5mm thick FR4 board using minimum copper 1 oz weight, 1mm wide tracks and one half of the device active is  $R_{th} = 250^\circ\text{C/W}$  giving a power rating of  $P_{tot} = 500\text{mW}$ .

# ZXTD4591AM832

## TYPICAL CHARACTERISTICS



# ZXTD4591AM832

## NPN TRANSISTOR

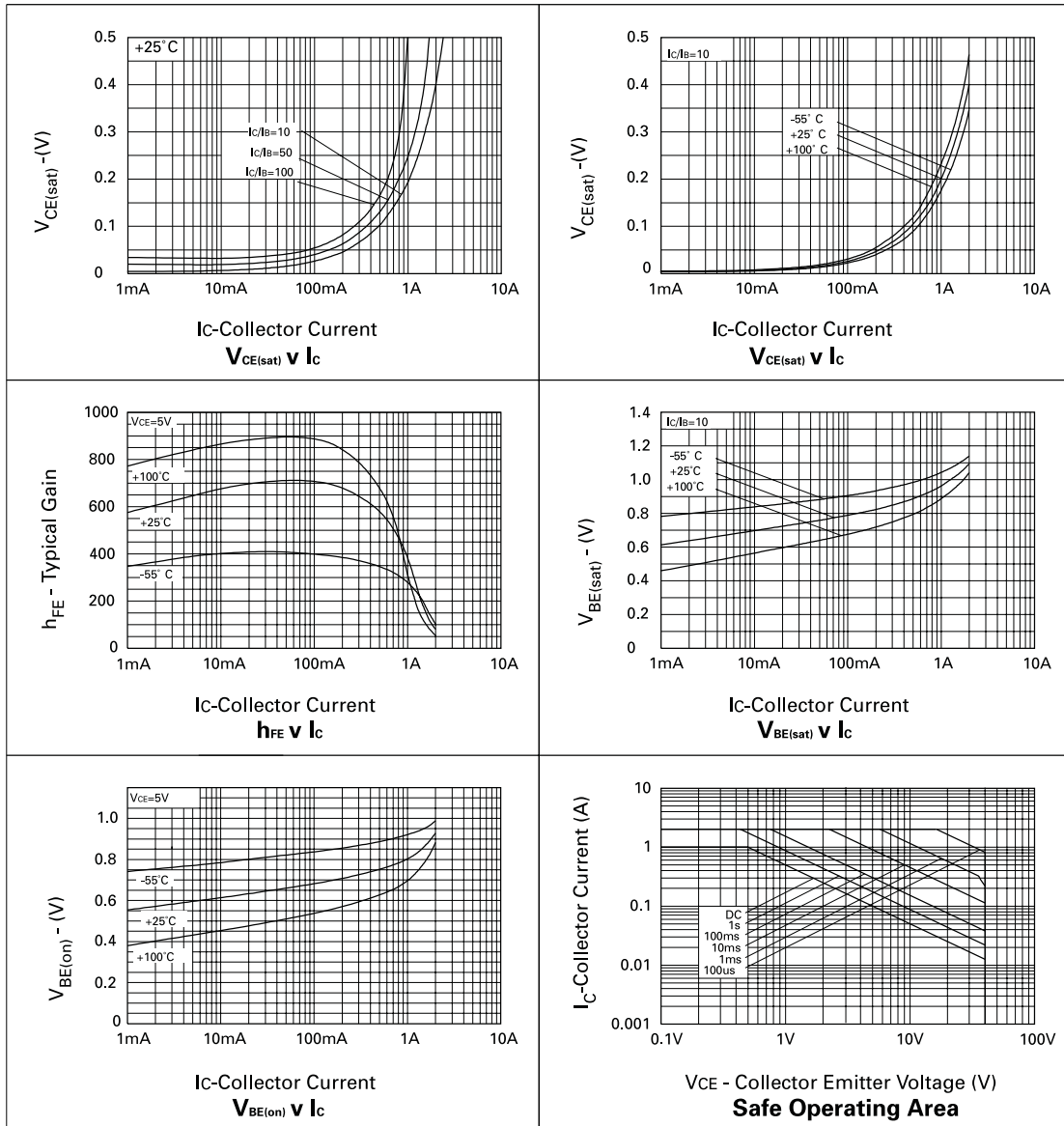
**ELECTRICAL CHARACTERISTICS** (at  $T_{amb} = 25^{\circ}\text{C}$  unless otherwise stated).

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS.
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	40			V	$I_C=100\mu\text{A}$
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	40			V	$I_C=10\text{mA}^*$
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	5			V	$I_E=100\mu\text{A}$
Collector Cut-Off Current	$I_{CBO}$			100	nA	$V_{CB}=30\text{V}$
Emitter Cut-Off Current	$I_{EBO}$			100	nA	$V_{EB}=4\text{V}$
Collector Emitter Cut-Off Current	$I_{CES}$			100	nA	$V_{CE}=30\text{V}$
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$			300 500	mV mV	$I_C=0.5\text{A}, I_B=50\text{mA}^*$ $I_C=1\text{A}, I_B=100\text{mA}^*$
Base-Emitter Saturation Voltage	$V_{BE(sat)}$			1.1	V	$I_C=1\text{A}, I_B=100\text{mA}^*$
Base-Emitter Turn-On Voltage	$V_{BE(on)}$			1.0	V	$I_C=1\text{A}, V_{CE}=5\text{V}^*$
Static Forward Current Transfer Ratio	$h_{FE}$	300 300 200 35		900		$I_C=1\text{mA}, V_{CE}=5\text{V}^*$ $I_C=0.5\text{A}, V_{CE}=5\text{V}^*$ $I_C=1\text{A}, V_{CE}=5\text{V}^*$ $I_C=2\text{A}, V_{CE}=5\text{V}^*$
Transition Frequency	$f_T$	150			MHz	$I_C=-50\text{mA}, V_{CE}=-10\text{V}$ $f=100\text{MHz}$
Output Capacitance	$C_{obo}$			10	pF	$V_{CB}=-10\text{V}, f=1\text{MHz}$

\*Measured under pulsed conditions.

# ZXTD4591AM832

## NPN TYPICAL CHARACTERISTICS



# ZXTD4591AM832

## PNP TRANSISTOR

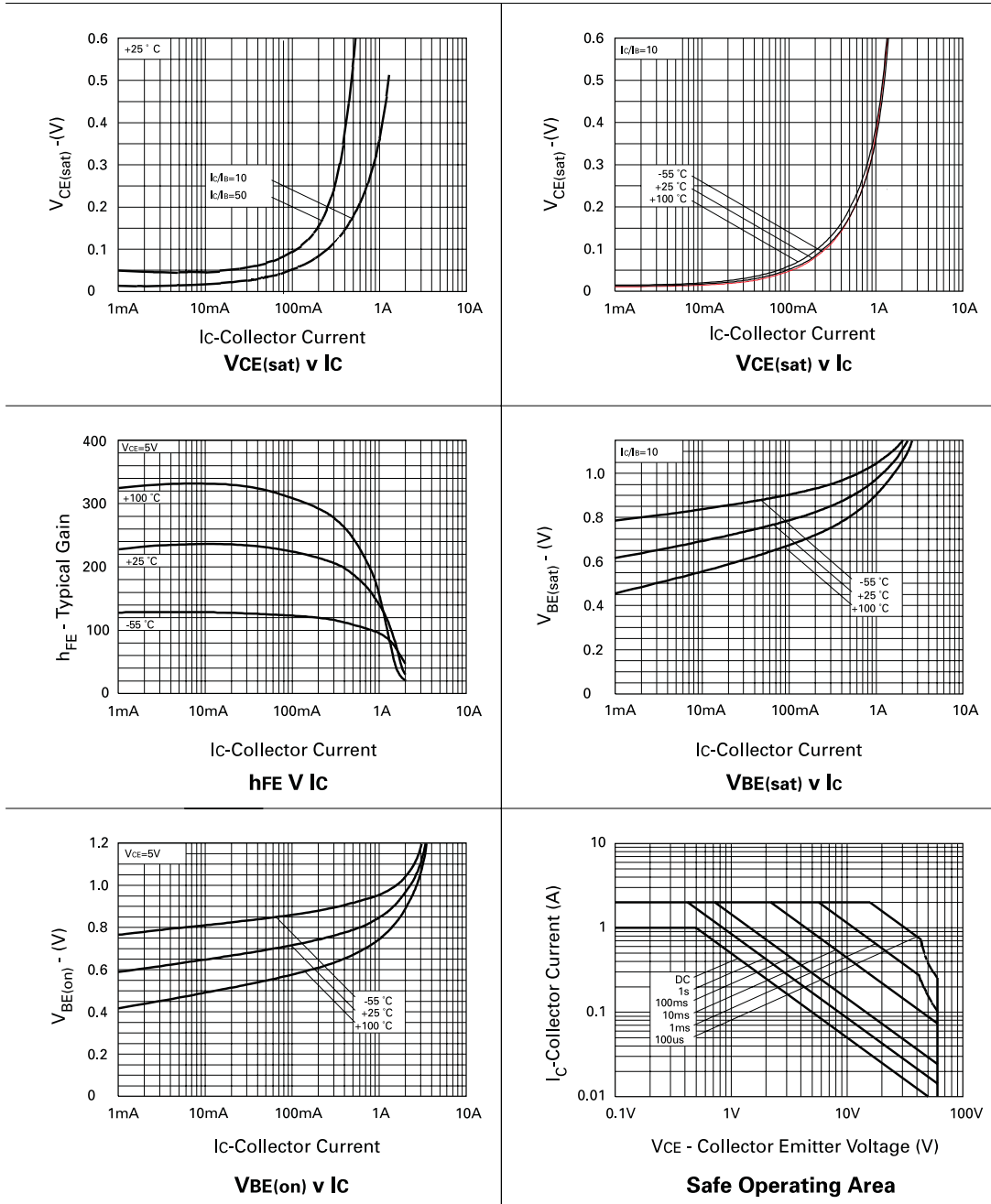
**ELECTRICAL CHARACTERISTICS** (at  $T_{amb} = 25^{\circ}\text{C}$  unless otherwise stated).

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS.
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	-40			V	$I_C = -100\mu\text{A}$
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	-40			V	$I_C = -10\text{mA}^*$
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	-5			V	$I_E = -100\mu\text{A}$
Collector Cut-Off Current	$I_{CBO}$			-100	nA	$V_{CB} = -30\text{V}$
Emitter Cut-Off Current	$I_{EBO}$			-100	nA	$V_{EB} = -4\text{V}$
Collector Emitter Cut-Off Current	$I_{CES}$			-100	nA	$V_{CE} = -30\text{V}$
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$			-200 -350 -500	mV mV mV	$I_C = -0.1\text{A}, I_B = -1\text{mA}^*$ $I_C = -0.5\text{A}, I_B = -20\text{mA}^*$ $I_C = -1\text{A}, I_B = -100\text{mA}^*$
Base-Emitter Saturation Voltage	$V_{BE(sat)}$			-1.1	V	$I_C = -1\text{A}, I_B = -50\text{mA}^*$
Base-Emitter Turn-On Voltage	$V_{BE(on)}$			-1.0	V	$I_C = -1\text{A}, V_{CE} = -5\text{V}^*$
Static Forward Current Transfer Ratio	$h_{FE}$	300 300 250 160 30		800		$I_C = -1\text{mA}, V_{CE} = -5\text{V}^*$ $I_C = -0.1\text{A}, V_{CE} = -5\text{V}^*$ $I_C = -0.5\text{A}, V_{CE} = -5\text{V}^*$ $I_C = -1\text{A}, V_{CE} = -5\text{V}^*$ $I_C = -2\text{A}, V_{CE} = -5\text{V}^*$
Transition Frequency	$f_T$	150			MHz	$I_C = -50\text{mA}, V_{CE} = -10\text{V}$ $f = 100\text{MHz}$
Output Capacitance	$C_{obo}$			10	pF	$V_{CB} = -10\text{V}, f = 1\text{MHz}$

\*Measured under pulsed conditions.

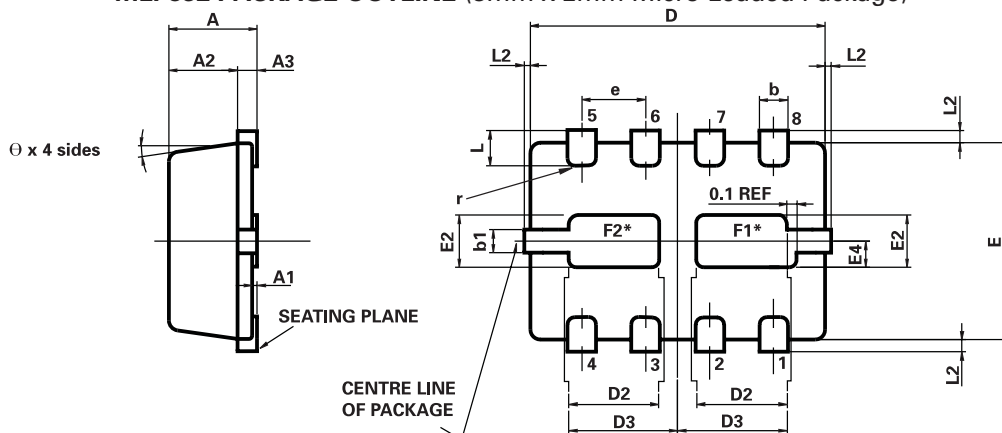
# ZXTD4591AM832

## PNP TYPICAL CHARACTERISTICS



# ZXTD4591AM832

## MLP832 PACKAGE OUTLINE (3mm x 2mm Micro Leaded Package)



\*Exposed Flags. Solder connection to improve thermal dissipation is optional.  
 F1 at collector 1 potential  
 F2 at collector 2 potential

CONTROLLING DIMENSIONS IN MILLIMETRES  
 APPROX. CONVERTED DIMENSIONS IN INCHES

### MLP832 PACKAGE DIMENSIONS

DIM	MILLIMETRES		INCHES		DIM	MILLIMETRES		INCHES	
	MIN.	MAX.	MIN.	MAX.		MIN.	MAX.	MIN.	MAX.
A	0.80	1.00	0.031	0.039	e	0.65 REF		0.0256 BSC	
A1	0.00	0.05	0.00	0.002	E	2.00 BSC		0.0787 BSC	
A2	0.65	0.75	0.0255	0.0295	E2	0.43	0.63	0.017	0.0249
A3	0.15	0.25	0.006	0.0098	E4	0.16	0.36	0.006	0.014
b	0.24	0.34	0.009	0.013	L	0.20	0.45	0.0078	0.0157
b1	0.17	0.30	0.0066	0.0118	L2	—	0.125	0.00	0.005
D	3.00 BSC		0.118 BSC		r	0.075 BSC		0.0029 BSC	
D2	0.82	1.02	0.032	0.040	θ	0°	12°	0°	12°
D3	1.01	1.21	0.0397	0.0476					

© Zetex plc 2002

#### Europe

Zetex plc  
 Fields New Road  
 Chadderton  
 Oldham, OL9 8NP  
 United Kingdom  
 Telephone (44) 161 622 4422  
 Fax: (44) 161 622 4420  
 uksales@zetex.com

Zetex GmbH  
 Streitfeldstraße 19  
 D-81673 München  
 Germany  
 Telefon: (49) 89 45 49 49 0  
 Fax: (49) 89 45 49 49 49  
 europe.sales@zetex.com

#### Americas

Zetex Inc  
 700 Veterans Memorial Hwy  
 Hauppauge, NY11788  
 USA  
 Telephone: (631) 360 2222  
 Fax: (631) 360 8222  
 usa.sales@zetex.com

#### Asia Pacific

Zetex (Asia) Ltd  
 3701-04 Metroplaza, Tower 1  
 Hing Fong Road  
 Kwai Fong  
 Hong Kong  
 Telephone: (852) 26100 611  
 Fax: (852) 24250 494  
 asia.sales@zetex.com

These offices are supported by agents and distributors in major countries world-wide.

This publication is issued to provide outline information only which (unless agreed by the Company in writing) may not be used, applied or reproduced for any purpose or form part of any order or contract or be regarded as a representation relating to the products or services concerned. The Company reserves the right to alter without notice the specification, design, price or conditions of supply of any product or service.

For the latest product information, log on to [www.zetex.com](http://www.zetex.com)



ISSUE 1 - JUNE 2002